



PATENT  
Atty Docket No. 2421-000030/US

**IN THE U.S. PATENT AND TRADEMARK OFFICE**

Applicant: Ja-Hum KU et al.

Appl. No.: 10/726,638

Group: 2812

Filed: December 4, 2003

Examiner: Booth, Richard

For: NICKEL ALLOY SALICIDE TRANSISTOR STRUCTURE AND  
METHOD FOR MANUFACTURING THE SAME

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October 25, 2007

**DECLARATION UNDER 37 CFR 1.132**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA

We, Ja-Hum Ku, Kwan Jong Roh, Min Chul Sun, and Min Joo Kim, hereby  
declare and state the following:

1. That we verily believe that we are the original, joint inventors of  
the invention of the above noted application;
2. That we are the authors of the article entitled "Thermally Robust  
Ta-Doped Ni SALICIDE Process Promising for sub-50nm CMOSFETs," which  
was published in October 2003;
3. That the information disclosed in the article was not known or  
used by others in this country, or patented or described in a printed  
publication in this or a foreign country, before the invention of the above  
noted application, U.S. Serial No. 10/726,638;

4. That the article is our own work, and that the co-authors C.S. Kim, S.P. Youn, S.-W. Jung, S. Choi, N.I. Lee, K.-K. Kang, and K.P. Sun assisted in experiments related to the Sun article accessorially or reviewed the Sun article;

5. That we are the joint inventors of the subject matter described and claimed in claims 1-34, and that the co-authors C.S. Kim, S.P. Youn, S.-W. Jung, S. Choi, N.I. Lee, K.-K. Kang, and K.P. Sun have not contributed conceptually to the subject matter in claims 1-34.

6. That it is declared by the undersigned that all statements made herein of undersigned's own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Title 18, U.S. Code 1001 and that such willful false statements may jeopardize the validity of this application or any patent issuing thereon.

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DATE

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Ja-Hum KU

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DATE

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Kwan Jong ROH

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DATE

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Min Chul SUN

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DATE

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Min Joo KIM